序號Serial No	20130201	3
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産品ITEM:	晶振		
型號TYPE:	TDXLF-206		
標稱頻率NOM	MINAL FREQUENCY:	32.768KHZ/12.5PF/±5ppm/≤35KΩ	

請收到我們的規格書後,簽字回傳。

Please confirm you received this specification, sign and fax it to us

接收確認RECEIVING CONFIRMATION				
日期DATA				
接收RECEIVED				

擬制Prepared by:	方浩
	dia to the
审核Checked by:	<u> </u>
批准Confirmed by:	王琴飞

RoHS Compliant Standard TD









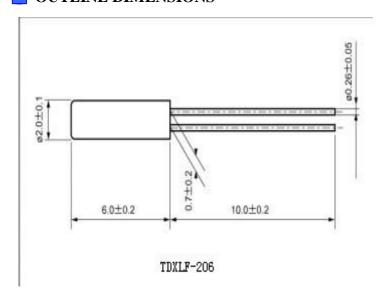
Features 特性

- Frequency Range:32.768KHz 頻率範圍: 32.768KHz
- Best suited for portable devices with low current consumption 非常適合低功耗的便攜設備
- For a clock source in digital equipments 適用於數碼設備的所有時鐘源

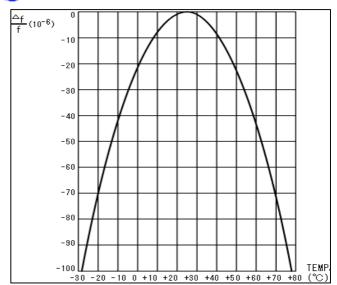
STANDARD SPECIFICATIONS 標準規格

Frequency Range	頻率範圍	32.768KHZ	Need to specify
Load Capacitance	負載電容	12.5pF	Need to specify
Drive Level	激勵電平	1.0μW Max	
Frequency Tolerance	調整頻差	±5ppm Max	at 25 [°] C Need to specify
Series Resistance	諧振電阻	35Kohm Max	at 25°C Depend on frequency
Turnover Temperature	拐點溫度	25±5°C	-
Temperature Coefficient	二次溫度係數	[-0.034±0.006]ppm/°(²	
Operating Temperature Range	e工作溫度範圍	−20~+70°C	
Storage Temperature Range	保存溫度範圍	–40~+85°C	
Motional Capacitance	動態電容	0.003pF Typical	和頻率有關Depend on frequency
Shunt Capacitance	靜態電容	1.35pF Typical	和頻率有關Depend on frequency
Capacitance Ratio	C0/C1	500 Typical	和頻率有關Depend on frequency
Aging[first year]	第一年老化率	±5ppm Max	25℃ ±3℃
Quality Factor	Q值	50000Typical	和頻率有關Depend on frequency
Insulation Resistance	絕緣阻扩	500Mohm Min.	DC100V±15V(Pin to Pin,Pin to case)

OUTLINE DIMENSIONS



FREQUENCY VS. TEMPERATURE CURVE



可靠性1Reliability(Mechanical and Environmental Endurance)

Page 1 c

No.Test ItemsTest Method and ConditionRequirements1振動(1)振動頻率Vibration Frequency 10 to 55Hz頻率變化最大:±10ppmVibration(2)振動幅度Vibration Amplitude 1.5mmFrequency Change:±10ppm(3)周期 Cycle Time 1-2min(10-55-10Hz)電阻變化最大:±15%或5kol(4)振動方向Direction X.Y.ZResistance Change:±15% or(5)振動時間Duration 2h/each direction5kohm Max.2衝撃從75cm高的地方自由跌落3次到30mm厚的硬木板上頻率變化最大:±10ppmShock3 Times free drop from 75cm height to hard woodenFrequency Change:±10ppmboard of thickness more than 30mm電阻變化最大:±15%或5kolResistance Change:±15% or5kohm Max.	nm Max.
Vibration (2)振動幅度Vibration Amplitude 1.5mm (3)周期 Cycle Time 1-2min(10-55-10Hz) (4)振動方向Direction X.Y.Z Resistance Change:±15% or (5)振動時間Duration 2h/each direction (2) 衝擊 從75cm高的地方自由跌落3次到30mm厚的硬木板上 (3) Times free drop from 75cm height to hard wooden board of thickness more than 30mm (2) 振動幅度Vibration Amplitude 1.5mm Frequency Change:±15% or 5kohm Max.	nm Max.
(3)周期 Cycle Time 1-2min(10-55-10Hz) 電阻變化最大:±15%或5koh (4)振動方向Direction X.Y.Z Resistance Change:±15% or (5)振動時間Duration 2h/each direction 5kohm Max. 2 衝擊 從75cm高的地方自由跌落3次到30mm厚的硬木板上 頻率變化最大:±10ppm 5hock 3 Times free drop from 75cm height to hard wooden board of thickness more than 30mm 電阻變化最大:±15%或5koh Resistance Change:±15% or 5kohm Max.	nm Max.
(4)振動方向DirectionX.Y.ZResistance Change:±15% or 5kohm Max.2 衝擊 Shock從75cm高的地方自由跌落3次到30mm厚的硬木板上 3 Times free drop from 75cm height to hard wooden board of thickness more than 30mm頻率變化最大:±10ppm Frequency Change:±10ppm 電阻變化最大:±15%或5kohm Max.	Max.
(5)振動時間Duration 2h/each direction 5kohm Max. 2 衝撃 從75cm高的地方自由跌落3次到30mm厚的硬木板上 頻率變化最大:±10ppm Shock 3 Times free drop from 75cm height to hard wooden board of thickness more than 30mm 電阻變化最大:±15%或5kohm Max. Resistance Change:±15% or 5kohm Max.	
2 衝擊 從75cm高的地方自由跌落3次到30mm厚的硬木板上 頻率變化最大:±10ppm Shock 3 Times free drop from 75cm height to hard wooden board of thickness more than 30mm 電阻變化最大:±15%或5koh Resistance Change:±15% or 5kohm Max.	
Shock 3 Times free drop from 75cm height to hard wooden board of thickness more than 30mm 電阻變化最大:±15%或5koh Resistance Change:±15% or 5kohm Max.	
board of thickness more than 30mm 電阻變化最大:±15%或5koh Resistance Change:±15% or 5kohm Max.	
Resistance Change:±15% or 5kohm Max.	nm
5kohm Max.	
3 氣密性 晶體放入氦加壓罐內,充入氦氣壓力0.5-0.6Mpa保持1小時; 漏氣率小於:1x10 ⁻ 8mbar.l/s	3
Leakage 然後使用氦質譜檢漏儀測試。 Leakage:1x10¯8mbar.l/s Ma	ıX.
Put crystal units into a hermetic container and Helium for 0.5-0.6	
Mpa, and keep it for 1h; Check the leakage by a Helium leak detector	
4 可焊性 將引線浸入完全熔化的焊錫鍋內3-5s,焊錫溫度245℃±5℃ 浸過引線面積的95%以上被	b新焊錫
Solderability Put the leads of crystal units into solder melted tank for 3 to 5s 覆蓋The dipped surface of the solder melted tank for 3 to 5s 覆蓋The dipped surface of the solder melted tank for 3 to 5s 覆蓋The dipped surface of the solder melted tank for 3 to 5s 覆蓋The dipped surface of the solder melted tank for 3 to 5s and 5s melted tank for 3 to 5s melted tank for 3	ne leads
Temperature of solder melted tank is 245°C±5°C should be at least 95% cover	ed with
continuous new solder coatir	ıg
5 引線強度(引線直插用0.9kg(9N)的力持續拉晶體引線30s±5s; 引線無異常	
晶體) 用0.45kg的力折引線成90℃次(折弯处离机体1.5mm以上); The crystal lead is not abnor	mity
Lead Strength(DIP) The crystal lead with the 0.9kg(9N)power(keep it for 30s±5s)	
and bend the crystal lead 90° with 0.45kg power and two times	
(which you want to bend should be more than 1.5mm from the	
case)	

			Page 2 o
	Test Items	Test Method and Condition	Requirements
	耐高溫能力	晶體放置於85℃±2℃環境中 2小時後,常溫放置1-2小時	頻率變化最大±10ppm
	High Temperature	The crystal units shall be put in somewhere for 2 hours at	Frequency Change:±10ppm Max.
	Endurance	temperature of $85^{\circ}\text{C} \pm 2^{\circ}\text{C}$, then keep it for 1 to 2 hours under room	
		temperature	Resistance Change:±15% or 5kohm Max
7	耐低溫能力	晶體放置於-25℃ 環境中2小時後,常溫放置1-2小時	
	Low Temperature	The crystal units shall be put in somewhere for 2 hours at	
	Endurance	temperature of -25°C, then keep it for 1 to 2 hours under room	
		temperature	
8	耐濕性	晶體放置於40℃、相對濕度90-95%環境中48小時後,常溫放	
	Humidity Endurance	置1-2小時The crystal units shall be put in somewhere at 40℃ in	
		relative humidity of 90-95% for 48 hours, then keep it for one or	
		two hours under room temperature	
9	高低溫迴圈	溫度從-40℃(保持30分鐘)升高到100℃(保持30分鐘),再	
	Temperature Cycle	到-40℃(保持30分鐘)然後回到室溫25℃完成一個迴圈,共	
		5個迴圈Temperature shift from low(-40℃) to high(100℃,keep 30	
		minutes),satisfy high(100°C) to low(-40°C,keep 30 minutes),then	
		go up to room temperature for 5 cycles	
10	鹽霧試驗	晶體置於鹽霧濃度5%,溫度35℃的鹽霧室中96小時後,用水	外觀良好, 可焊性良好
	Salt Spray Test	洗淨擦幹表面	The appearance shall has no abnormity
		Put the crystal units in the salt spray room(salt density:5%)at the	and soldering is good.
		temperature of 35°C for 96 hours. Then clean it with water and dry	頻率變化最大±10ppm
		its surface.	Frequency Change:±10ppm Max.
			電阻變化最大:±10%或5kohm
			Resistance Change:±10% or 5kohm Max
11	波峰焊	对于插脚型晶体推荐使用下面的波峰焊温度曲线进行波峰焊接	頻率變化最大±10ppm
	Wave soldering	For DIP type crystal resonator, The WAVE SOLDERING PROFIL	Frequency Change:±10ppm Max.
		as below is recommended:	電阻變化最大:±10%或5kohm
			Resistance Change:±10% or 5kohm Max
			C
		270± 5℃ /65 Max.	
		0 260 ==================================	
		1ST WAVE	
		₩ / 5°C/SEC	
		5	
		∀ 209°C/SEC /	
		K	
		Q 100	
		D 260 1ST WAVE 200°C/SEC 2	
		25	
		-1.5 100 SEC 100	
		TIME (SEC)	

使用說明Processing Instructions

下面的說明和資訊供用戶正確理解和使用我們公司的石英晶體系列產品,預防不當的加工方式對石英晶體的損壞,確保用戶設備的可靠性

The following instructions and information are provided for the purpose of having the user understand the proper way to process our crystal products to prevent problems prior to use and enhance the reliability of the equipment to which they are applied.

PROCESSING INSTRUCTIONS

石英晶體意外跌落When dropped by mistake

設計和製造的石英晶體本身具有耐衝擊能力,但是當石英晶體元件經受劇烈的機械衝擊,如跌落到地板上或安裝期間劇烈 動時,在使用之前需要進行電性能確認

The crystal units are designed and manufactured to resist physical shocks. However, when the crystal units are subjected to excessive impact such as being dropped onto the floor or giving shocks during processing, need to make sure its satisfactory performance before using it.

2 焊接Soldering

No.

(1)引線型産品Lead Type products

a.使用電烙鐵焊接時,引線應該在5秒內焊接完畢,電烙鐵溫度不能高於300℃

Lead wires should be soldered within 5 seconds with the soldering iron heated to a temperature no higher than 300° C

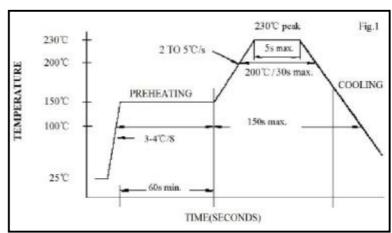
b.使用波峰焊接方式時,引線應該在6秒內焊接完畢,焊錫溫度不能高於275℃,並且注意不能將整個晶體浸錫.推薦使用垂直安裝方式,避免熱力直接傳導到晶體上

In WAVE solder processing, the leads should be soldered within 6 seconds with a temperature no higher than 275°C. Mounting in upright is recommendable to prevent the heat conduction directly to the body of the crystal unit.

(2)SMD產品SMD Type products

a.TMXLF-206/206F/206FS/206FA02/AT309/AT309F產品系列推薦使用下面的回流焊曲線

The REFLOW SOLDERING PROFILE as below is recommended for TMXLF-206/206F/206FS/206FA02 /AT309 /AT309Ffamilie



使用說明Processing Instructions

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PROCESSING INSTRUCTIONS

3 | 石英晶體彎腳TO BEND THE LEAD of cylinder type products

(1)當圓柱狀晶體元件需要彎腳時,爲了防止彎腳時造成密封玻璃體的破裂,從彎腳處到晶體基座底部距離應大於1.5mm。 薦距離3.0mm,並使用工裝夾具進行彎腳。

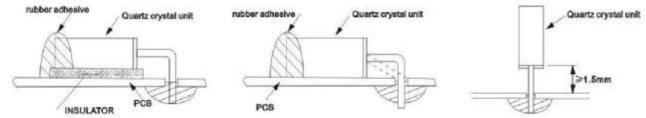
When the lead of cylinder type crystal units need to be bent,leave more than 1.5mm(3.0mm is recommendable) of lead from the case in order to prevent from any cracks of the hermetic sealing glass at the root of the lead,and use a jig to bend if possible. (2)當圓柱狀晶體元件進行彎腳時,不要剝離引線的鍍層

When bending the lead of cylinder type crystal units, do not scrape off the soldering plating from the lead surface.

4 元件的安裝MOUNTING

4.1圓柱狀晶體元件的安裝MOUNTING of cylinder type products

(1)爲了避免影響元件電性能或損壞元件,嚴禁將圓柱狀晶體元件外殼焊接在印製板上進行固定。推薦使用橡膠粘結劑進行固定Soldering the body of the cylinder type crystal units with PCB must be avoided due to deteriorate the characteristics or damage the products.Rubber adhesive is recommended



(2)當用手工來彎曲引線時,請遵照下列方法When the lead needs to be bent by hand, please follow the instruction as below:

用手指捏住圓柱晶體的外殼;用鑷子夾住引線要彎曲的部位,該部位離晶體基座底部1.5mm以上(推薦3.0mm);

用鑷子夾住彎曲引線成90°,不要用力拉引線。用力拉引線可能造成引線根部的玻璃子破裂,而產生漏氣損壞元件電性能。

Hold the body of the cylinder type crystal unit in fingers;

Pick at the part with tweezer, which you want to bend. There should be more than 1.5mm(3.0mm is recommended) from the body case Bend the lead 90° by tweezer without pulling the lead strongly. If pulling the lead strongly may cause any cracks of hermetic sealing glass at the root of the lead and may cause the leakage and the characteristics to deteriorate.

4.2 SMD晶體元件的安裝MOUNTING of SMD TYPE products

當使用自動安裝設備來裝配SMD晶體元件時,裝配之前要檢測自動安裝設備不會損壞元件。

安裝和焊接晶體元件後,由於機械張力,分裂開整塊線路板産生的線路板的彎曲將造成焊接的脫離或晶體元件封裝的裂開 請確保晶體元件在線路板上的焊盤位置産生的焊接應力較小和分裂線路板對晶體元件產生的應力較小。

When using an automatic loading machine, please test and confirm to cause no damage to the crystal units before mounting.

Bending the circuit board in the process of cleaving boards after mounting and soldering crystal units may cause peeling off the soldering or package cracks by mechanical stress.

Please be sure that the layout of crystal products position is on the less sressed and the cleaving process is under less stessed for the crystal units.

5 |石英晶體元件的清洗CLEANING

(1)惡劣的超聲波清洗或超聲波焊接可能會影響和損壞石英晶體元件。如果您對晶體元件進行了超聲波清洗,請一定在使用確認品體元件是否受到了影響和損壞

Crystal units may be sffected and destroyed at worst by supersonic cleaning or supersonic welding. Please be sure to check if your cleaning and welding process sffects any damage to crystal units before using.

(2)有些清洗液也可能造成晶體元件的損壞,請在使用清洗液前確認該清洗液是否適用

Some kinds of cleaning fluid may cause any damage to crystal units. Please be sure to check suitability of the cleaning fluid in advan-

6 貯存STORAGE

石英晶體元件長時間貯存在高溫或高濕環境中,可能會影響頻率的穩定性或可焊性。請將晶體元件貯存在正常的溫度和濕環境中,避免陽光直射和露水凝結,避免貯存6個月以上再使用,拆封後儘快裝配使用。

Storage of crystal units under higher temperature or high humidity for a long term may affects frequency stability or solderability. Please store the crystal units under the normal temperature and humidity without exposing to direct sunlight and dew condensation, and avoid the storage of crystal units for more than 6 months, and mount them as soon as possible after unpacking.

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